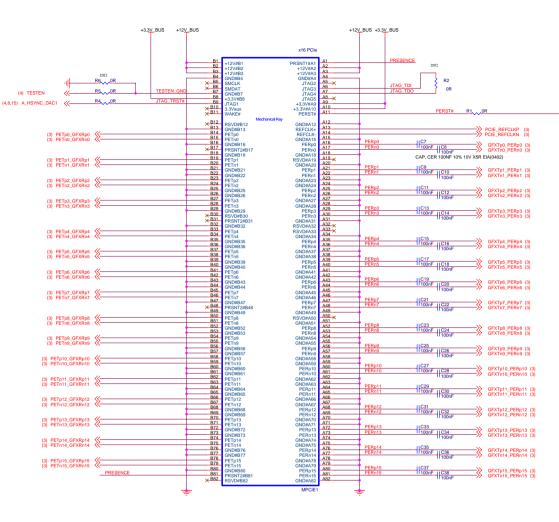


PCI-EXPRESS EDGE CONNECTOR



Power Sequence Circuit to ensure SMPS_EN is released after +12V_BUS and +3.3V_BUS are both in regulation.
Pull-up may or may not be required on SMPS_EN signal depending on SMPS design.

Node 1 When +12V ramps above min Vbe, SMPS_EN will be helt low Node 2 When +3.3V gets close to regulation, one of the two conditions of releasing SMPS_EN is active

Target ~ 900mV when +3.3 at min regulation (worse case)
Typical trigger when +3.3V ramps above 2.2V (650mV)

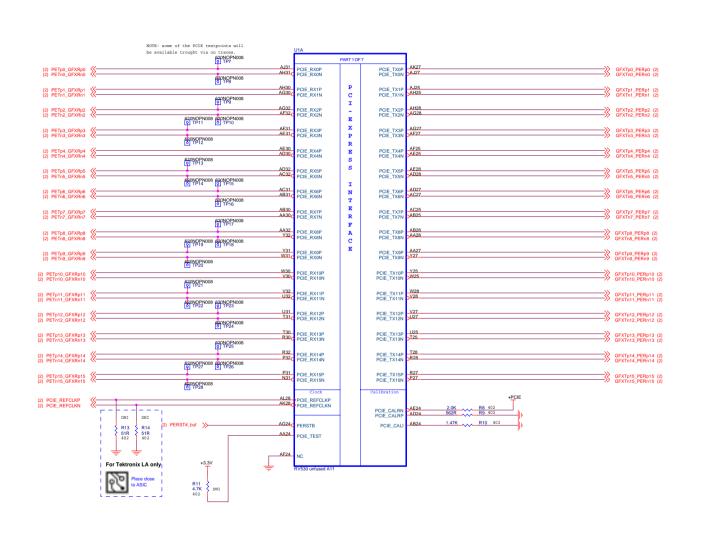
Node 3 When +12V gets close to regulation, one of the two conditions of releasing SMPS_EN is active

Target ~ 1.25V when +12 at min regulation (worse case)
Typical trigger when +12V ramps above 10V (1.1V)

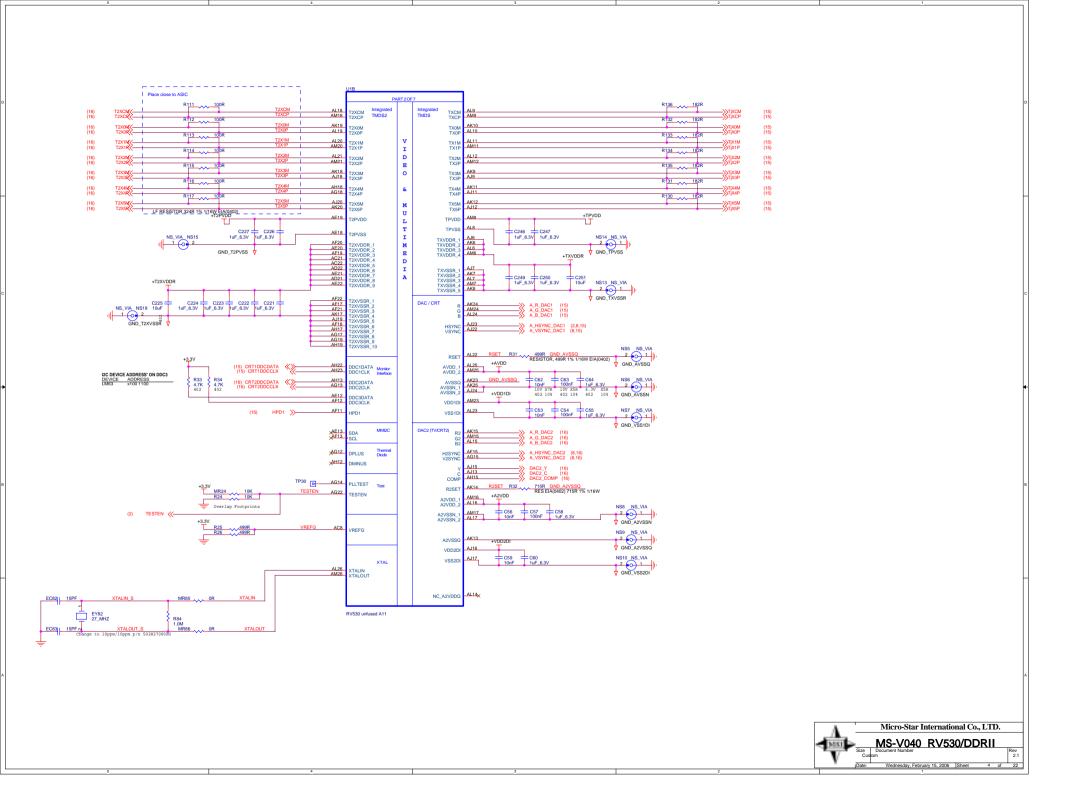


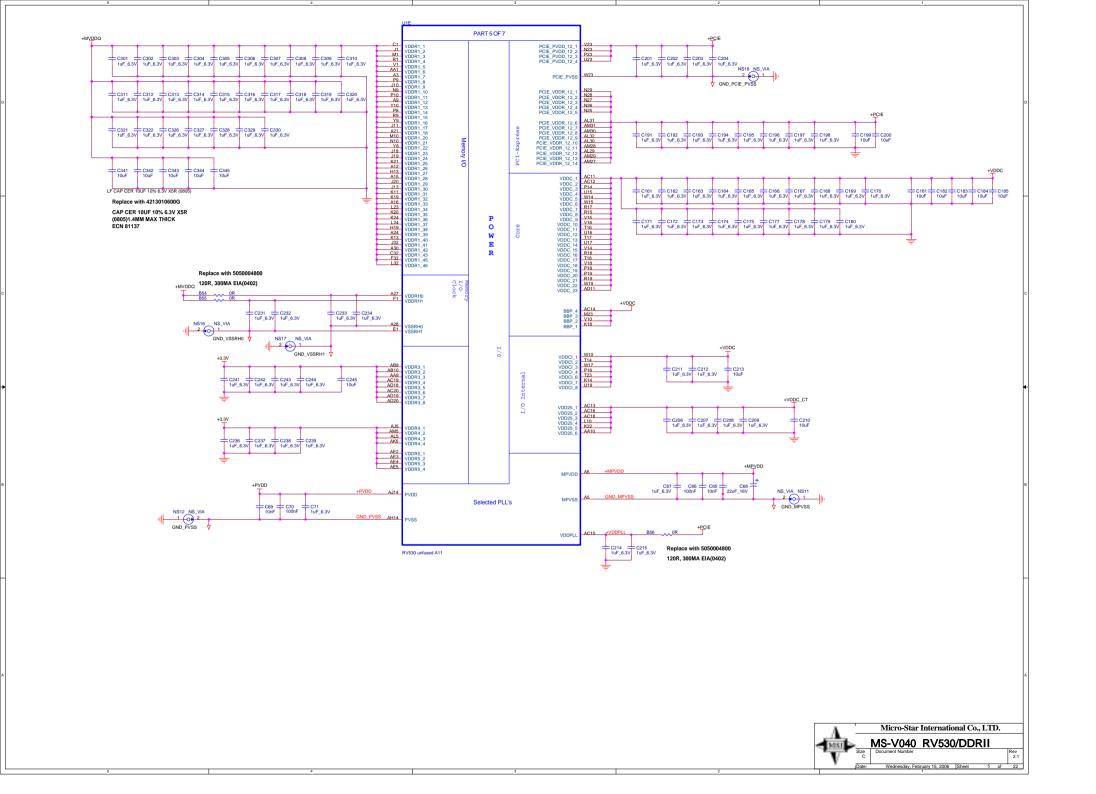
CAP CERAMIC 100NE 10% 10V X5R EIA(0402)





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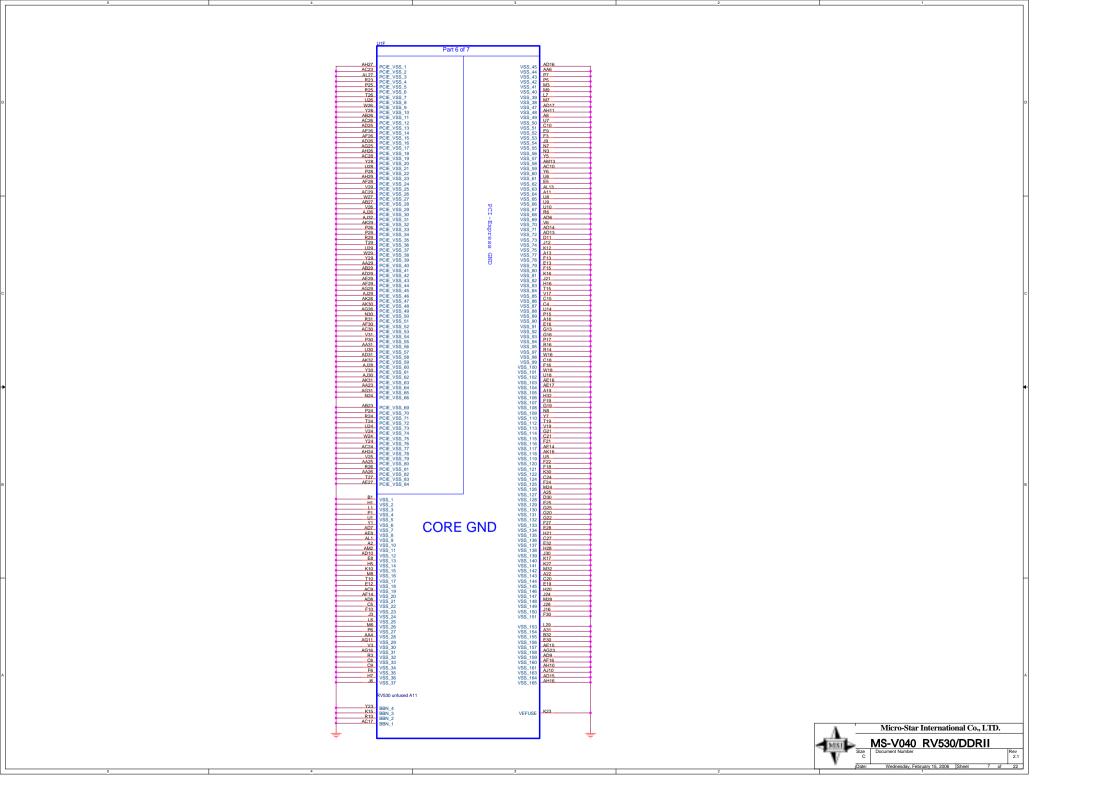
RV530 MEMORY CHANNELS A and B Channel B Channel A (14) M_MDB[63..0] «>> M_MAB[12..0] (14) Part 4 of 7 (13) M_MDA[63..0] «> →>> M_MAA[12..0] (13) Part 3 of 7 M31 DOA, 0 M30 DOA, 1 L30 DOA, 2 L30 DOA, 2 L30 DOA, 2 L30 DOA, 3 L30 DOA, 2 L30 DOA, 3 L30 DOA, 2 L30 DOA, 3 L30 DOA, 5 L30 DOA, 10 L30 MAA_0 MAA_1 MAA_2 MAA_3 MAA_6 MAA_6 MAA_7 MAA_1 MAA_1 MAA_1; MAA_1; MAA_1; MAA_1; MEMORY INTERFACE A MEMORY INTERFACE B M_MAA[15..14] (13) >>> M_DQMA#[7..0] (13) DQMBb DQMBb DQMBb DQMBb DQMBb DQMBb DQMBb DQMBb DQMBb DQMAb_C DQMAb_C DQMAb_C DQMAb_C DQMAb_C DQMAb_C DQMAb_C ✓ M_QSB[7..0] (14) ✓ M_QSA[7..0] (13) QSB_0 QSB_1 QSB_2 QSB_3 QSB_4 QSB_5 QSB_6 QSB_7 QSA_G QSA_G QSA_G QSA_G QSA_G QSA_G QSB_0B QSB_1B QSB_2B QSB_3B QSB_4B QSB_5B QSB_6B QSB_7B QSA_0B QSA_1B QSA_2B QSA_3B QSA_4B QSA_5B QSA_6B QSA_7B ODTB0 $\begin{array}{c} \text{ODTA0} \\ \text{ODTA1} \end{array}$ $\begin{array}{c} \text{D24} \\ \times \end{array}$ $\begin{array}{c} \text{ODTA0} \end{array}$ (13) For DDR2 CLKB0 CLKB0b C2 >>> CKEB0 CKEB0 CKEA0 _B30 _______ CKEA0 (13) o^{E2}→>> RASB#0 RASB0b RASA0b 0B28 >>> RASA#0 (13) CASB0b DD3 CASB#0 CASA0b DC29 >>> CASA#0 (13) +MVDDQ WEB0b DB2 >> WEB#0 +MVDDQ (14) WEA0b 0B31 >>> WEA#0 (13) CLKA1 CLKA1 (13) CLKA1b CLKA#1 (13) C351 C352 100nF 10nF CKEB1 13 CKEB1 R162 100R 1% (14) CKEA1 C22 >>> CKEA1 (13) C355 C356 100nF 10nF RASB1b OJ2 >>> RASB#1 (14) DRAM RST RASA1b 0B24 >>> RASA#1 (13) CASB1b OL2 >>> CASB#1 (14) TEST MOLK CASA1b 0B22 >>> CASA#1 (13) WEB1b 0M2_>> WEB#1 TEST_YCLK WEA1b 0B21 >>> WEA#1 (13) K2_→> CSB#1_0 (14) MEMTEST

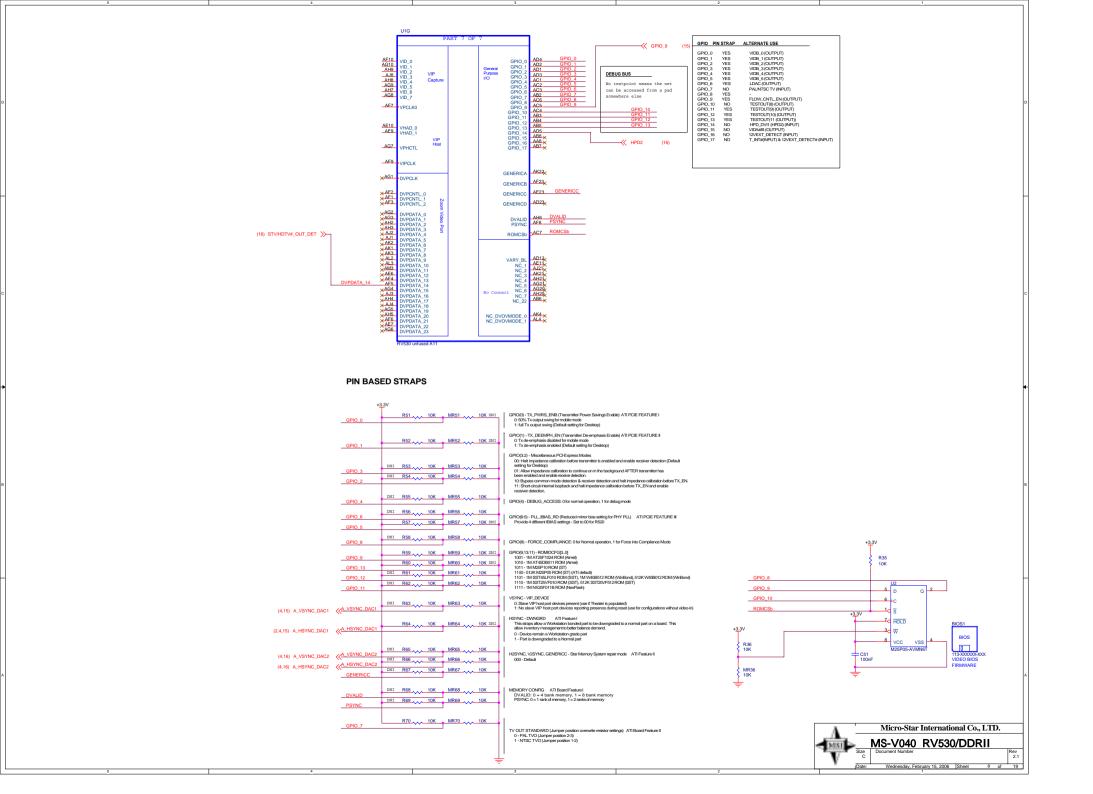
R172 R171 R170 4.7K 4.7K 4.7K

RESISTOR, 4.7K 5% 1/16W EIA(0402)

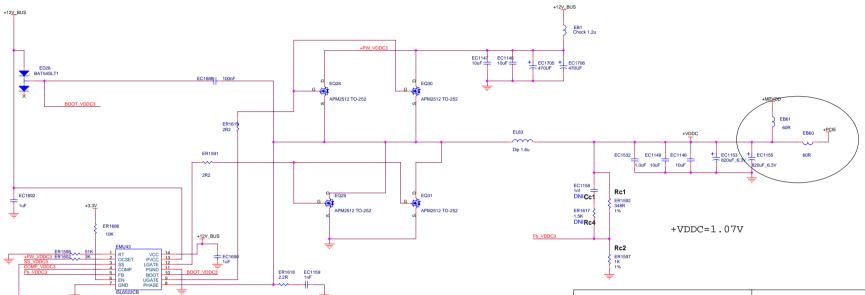
R169 > 243R LF RES EIA(0402) 243R 1% 1/16W





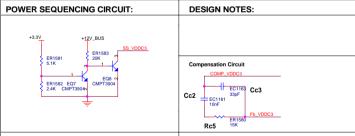


CORE REGULATOR VDDC



Lower MOSFET should be surrounded by a lot of copper for heat dissipation

ISL6522CB : SOIC ISL6522CV : TSSOF



FOR ALTERNATE #1

FOR ALTERNATE #2

Remove R374, R375, R371, C168 and U32 Change C157 for 10 uF and C121 for 1 uF Replace C764 by 0 Ohm resistor Install R370, R112, R954, R305-R308, C15Replace R314 with a bead C159 and MU32

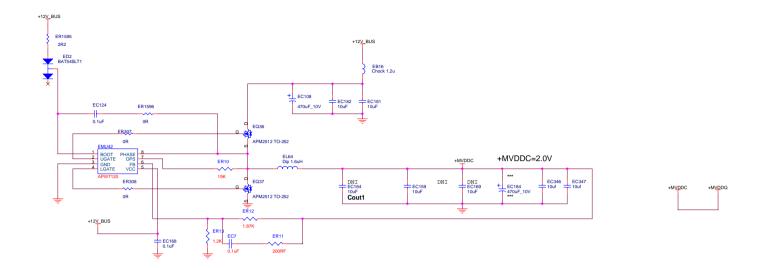
Remove R954, R370, R305-R308, C159, R112, C160 and MU32

Install R374, R375, R371, C168 and U32

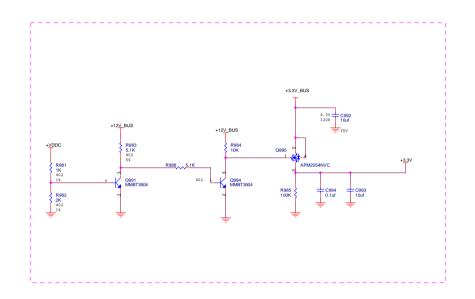
Compensation circuit

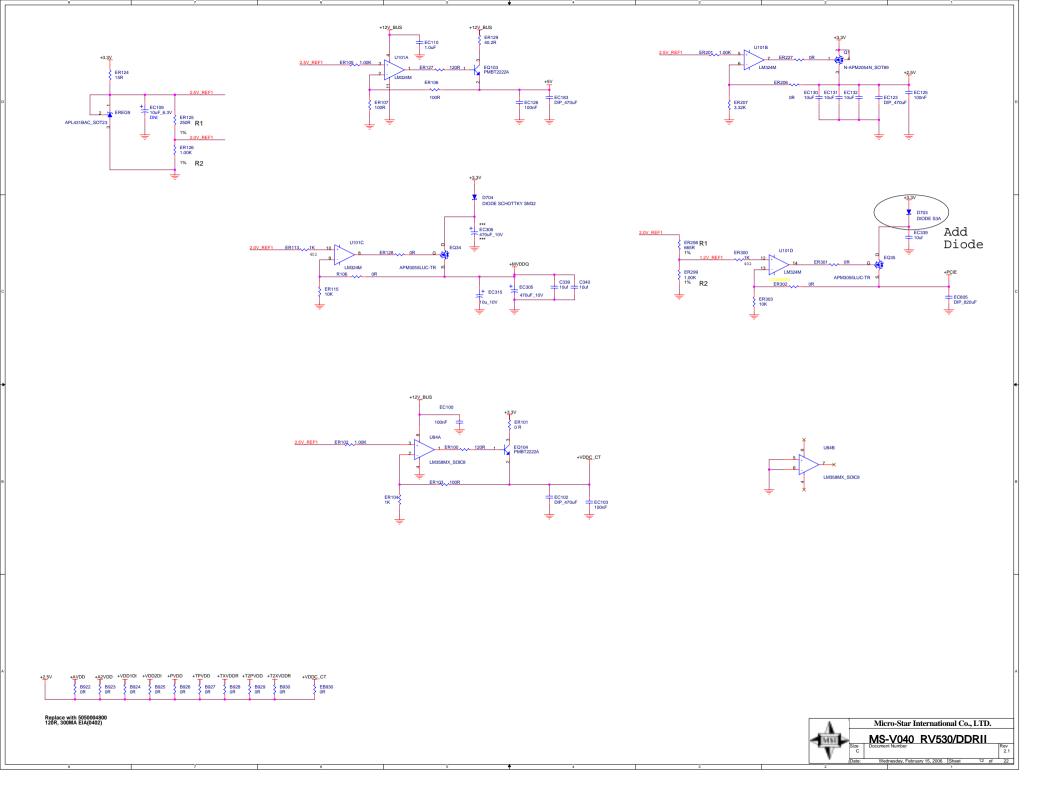
Rc1 = 10K, Rc2 = 8.06K R313 = 93.1K, C171 = 3.9 nF, C170 = 10 pF



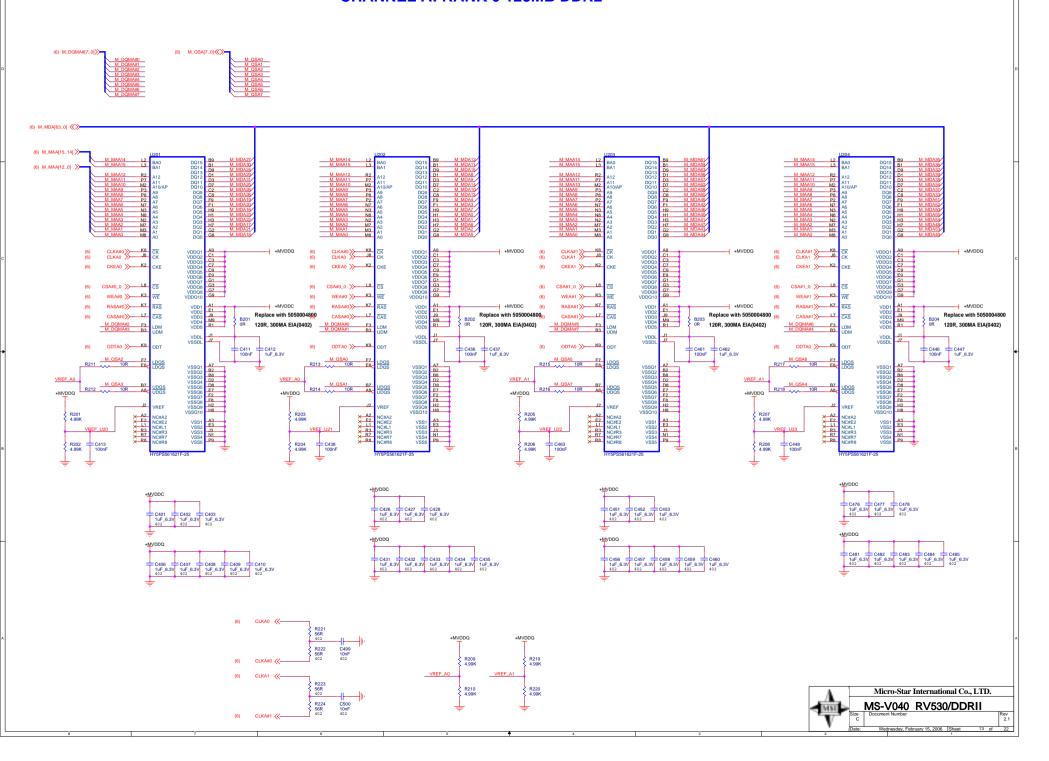


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CHANNEL A: RANK 0 128MB DDR2



CHANNEL B: RANK 0 128MB DDR2

